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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE	<i>Application No.</i>	10/024,475
	<i>Filing Date</i>	December 21, 2001
	<i>First Named Inventor</i>	Chan-ho PARK
	<i>Group Art Unit</i>	2811
	<i>Examiner Name</i>	Ori Nadav
	<i>Attorney Docket No.</i>	1751-294
<i>Title of the Invention:</i> HIGH VOLTAGE SEMICONDUCTOR DEVICE HAVING HIGH BREAKDOWN VOLTAGE AND METHOD OF FABRICATING THE SAME		

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RESPONSE TO RESTRICTION REQUIREMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the restriction requirement mailed August 23, 2002, Applicant hereby elects Group I, consisting of claims 1-3, drawn to a semiconductor device, classified in class 257, subclass 341. Applicant reserves the right to pursue the non-elected claims in a divisional application.

Favorable action on the elected claims is earnestly solicited.

RESPECTFULLY SUBMITTED,					
NAME AND REG. NUMBER	Monica S. Davis, Registration No. 44,492				
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